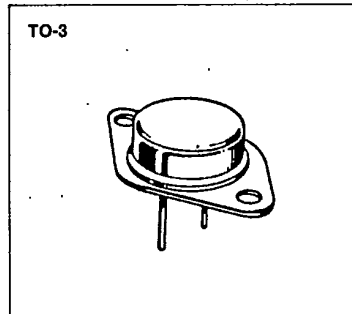
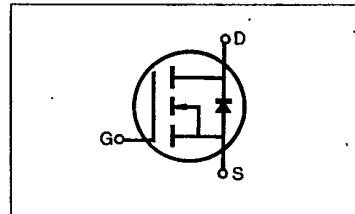


IRF250/251/252/253**N-CHANNEL
POWER MOSFETS****FEATURES**

- Low $R_{DS(on)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Low input capacitance
- Extended safe operating area
- Improved high temperature reliability
- TO-3 package (High current)

**PRODUCT SUMMARY**

Part Number	V _{DS}	R _{DS(on)}	I _D
IRF250	200V	0.085 Ω	30A
IRF251	150V	0.085 Ω	30A
IRF252	200V	0.12 Ω	25A
IRF253	150V	0.12 Ω	25A

**MAXIMUM RATINGS**

Characteristic	Symbol	IRF250	IRF251	IRF252	IRF253	Unit
Drain-Source Voltage (1)	V _{DSS}	200	150	200	150	V _{dc}
Drain-Gate Voltage (R _{GS} =1.0M Ω) (1)	V _{DGR}	200	150	200	150	V _{dc}
Gate-Source Voltage	V _{GS}	± 20				V _{dc}
Continuous Drain Current T _C =25°C	I _D	30	30	25	25	A _{dc}
Continuous Drain Current T _C =100°C	I _D	19	19	16	16	A _{dc}
Drain Current—Pulsed (3)	I _{DM}	120	120	100	100	A _{dc}
Gate Current—Pulsed	I _{GM}	± 1.5				A _{dc}
Total Power Dissipation @ T _C =25°C	P _D	150				Watts
Derate above 25°C		1.2				W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150				°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T _L	300				°C

Notes: (1) T_J=25°C to 150°C

(2) Pulse test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

(3) Repetitive rating: Pulse width limited by max. junction temperature

IRF250/251/252/253

N-CHANNEL
POWER MOSFETSELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise specified)

Characteristic	Symbol	Type	Min	Typ	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	IRF250 IRF252	200	—	—	V	V _{GS} =0V
		IRF251 IRF253	150	—	—	V	I _D =250μA
		ALL	—	—	—	—	V _{DS} =V _{GS} , I _D =250μA
Gate Threshold Voltage	V _{GS(th)}	ALL	2.0	—	4.0	V	V _{DS} =V _{GS} , I _D =250μA
Gate-Source Leakage Forward	I _{GSS}	ALL	—	—	100	nA	V _{GS} =20V
Gate-Source Leakage Reverse	I _{GSS}	ALL	—	—	-100	nA	V _{GS} =-20V
Zero Gate Voltage Drain Current	I _{DSS}	ALL	—	—	250	μA	V _{DS} =Max. Rating, V _{GS} =0V
			—	—	1000	μA	V _{DS} =Max. Rating×0.8, V _{GS} =0V, T _C =125°C
On-State Drain-Source Current (2)	I _{D(on)}	IRF250 IRF251	30	—	—	A	V _{DS} >I _{D(on)} ×R _{DS(on) max.} , V _{GS} =10V
		IRF252 IRF253	25	—	—	A	
		ALL	—	—	—	—	
Static Drain-Source On-State Resistance (2)	R _{DS(on)}	IRF250 IRF251	—	0.07	0.085	Ω	V _{GS} =10V; I _D =16A
		IRF252 IRF253	—	0.09	0.120	Ω	
		ALL	—	—	—	—	
Forward Transconductance (2)	g _{fs}	ALL	8.0	12.5	—	Ω	V _{DS} >I _{D(on)} ×R _{DS(on) max.} , I _D =16A
Input Capacitance	C _{iss}	ALL	—	2640	3000	pF	V _{GS} =0V, V _{DS} =25V, f=1.0MHz
Output Capacitance	C _{oss}	ALL	—	800	1200	pF	
Reverse Transfer Capacitance	C _{rss}	ALL	—	300	500	pF	
Turn-On Delay Time	t _{d(on)}	ALL	—	—	35	ns	V _{DD} =0.5BV _{DSS} , I _D =16A, Z _O =4.7 Ω (MOSFET switching times are essentially independent of operating temperature.)
Rise Time	t _r	ALL	—	—	100	ns	
Turn-Off Delay Time	t _{d(off)}	ALL	—	—	125	ns	
Fall Time	t _f	ALL	—	—	100	ns	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q _g	ALL	—	68	120	nC	V _{GS} =10V, I _D =38A, V _{DS} =0.8 Max. Rating (Gate charge is essentially independent of operating temperature.)
Gate-Source Charge	Q _{gs}	ALL	—	18	—	nC	
Gate-Drain ("Miller") Charge	Q _{gd}	ALL	—	50	—	nC	

THERMAL RESISTANCE

Junction-to-Case	R _{thJC}	ALL	—	—	0.83	K/W	
Case-to-Sink	R _{thCS}	ALL	—	0.1	—	K/W	Mounting surface flat, smooth, and greased
Junction-to-Ambient	R _{thJA}	ALL	—	—	30	K/W	Free Air Operation

Notes: (1) T_J=25°C to 150°C

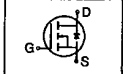
(2) Pulse test: Pulse width≤300μs, Duty Cycle≤2%

(3) Repetitive rating: Pulse width limited by max. junction temperature

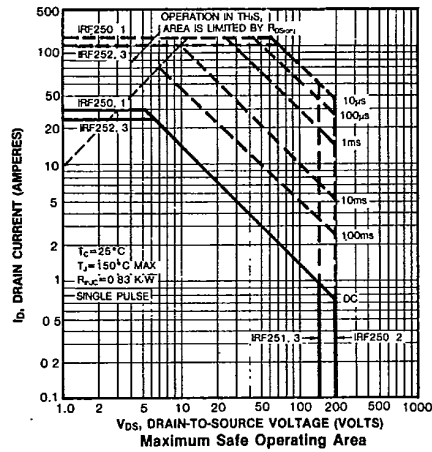
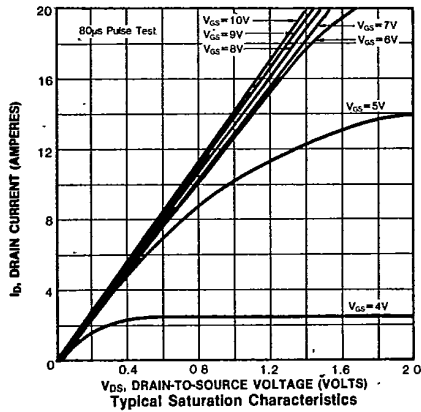
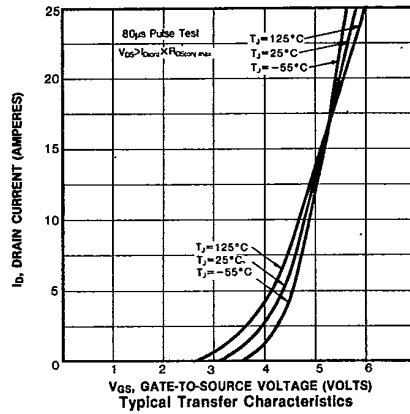
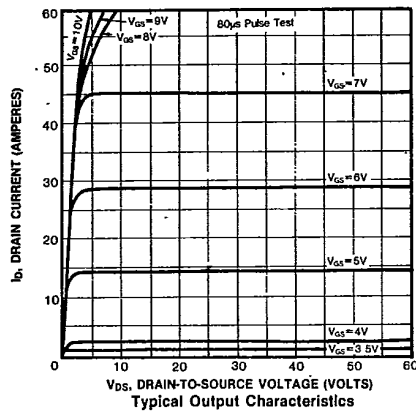
IRF250/251/252/253

**N-CHANNEL
POWER MOSFETS**

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

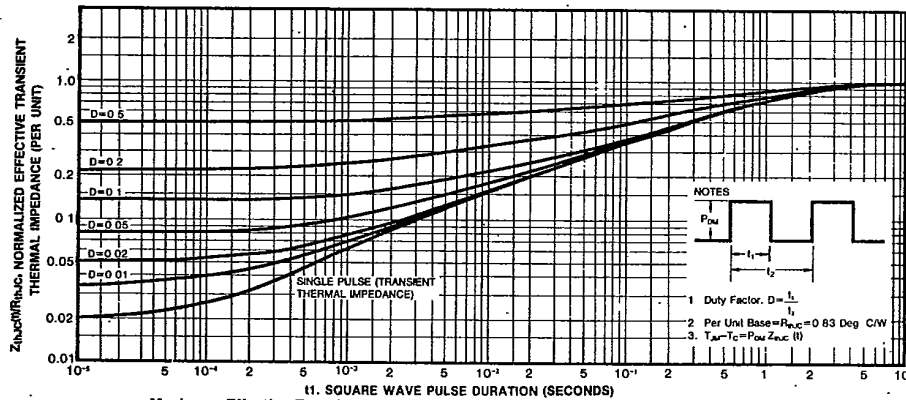
Characteristic	Symbol	Type	Min	Typ	Max	Units	Test Conditions
Continuous Source Current (Body Diode)	I _S	IRF250	—	—	30	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier 
		IRF251	—	—	30	A	
		IRF252	—	—	25	A	
		IRF253	—	—	25	A	
Pulse Source Current (Body Diode) (3)	I _{SM}	IRF250	—	—	120	A	
		IRF251	—	—	120	A	
		IRF252	—	—	100	A	
		IRF253	—	—	100	A	
Diode Forward Voltage (2)	V _{SD}	IRF250	—	—	2.0	V	T _C =25°C, I _S =30A, V _{GS} =0V
		IRF251	—	—	2.0	V	
		IRF252	—	—	1.8	V	
Reverse Recovery Time	t _{rr}	ALL	—	750	—	ns	T _J =150°C, I _F =30A, dI _F /dt=100A/μs

Notes: (1) T_J=25°C to 150°C (2) Pulse test: Pulse width≤300μs, Duty Cycle≤2%
(3) Repetitive rating: Pulse width limited by max. junction temperature

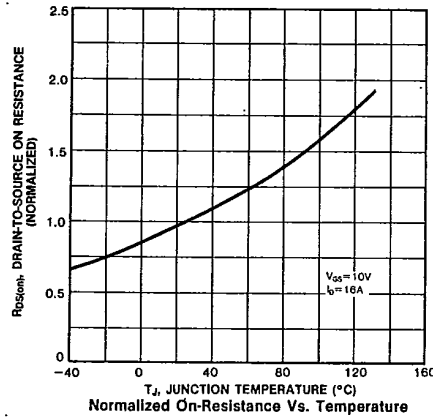
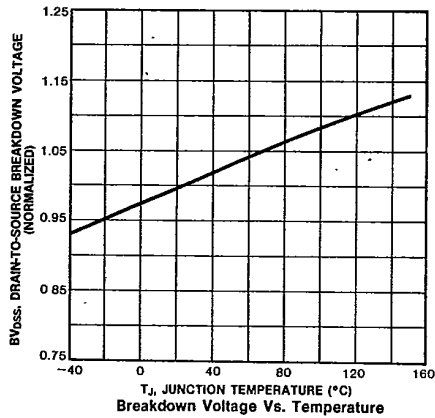
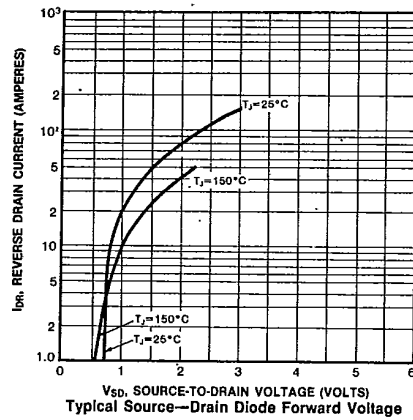
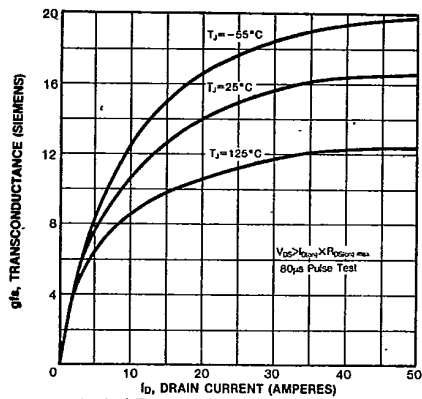


IRF250/251/252/253

N-CHANNEL POWER MOSFETS



Maximum Effective Transient Thermal Impedance Junction-to-Case Vs. Pulse Duration



IRF250/251/252/253

N-CHANNEL
POWER MOSFETS

